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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/904,360	07/12/2001	Giuseppe Curello	Z&PINFP-08190	1413	
24131 75	90 09/21/2004		EXAM	EXAMINER	
LERNER AND GREENBERG, PA			ANYA, IGWE U		
P O BOX 2480	o, FL 33022-2480		ART UNIT	PAPER NUMBER	
HOLLI WOOL	, 11 33022 2100		2825		
			DATE MAILED: 09/21/200	4	

Please find below and/or attached an Office communication concerning this application or proceeding.

•	Application No.	Applicant(s)	
	09/904,360	09/904,360 CURELLO ET AL.	
Office Action Summary	Examiner	Art Unit	
	Igwe U. Anya	2825	كرمهم
The MAILING DATE of this communication Period for Reply	appears on the cover sheet	with the correspondence add	ress
A SHORTENED STATUTORY PERIOD FOR RETHE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CF after SIX (6) MONTHS from the mailing date of this communication - If the period for reply specified above is less than thirty (30) days, and If NO period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by so Any reply received by the Office later than three months after the nearned patent term adjustment. See 37 CFR 1.704(b).	DN. R 1.136(a). In no event, however, may n. a reply within the statutory minimum of eriod will apply and will expire SIX (6) N tatute, cause the application to become	v a reply be timely filed thirty (30) days will be considered timely. IONTHS from the mailing date of this come ABANDONED (35 U.S.C. § 133).	munication.
Status			
 1) Responsive to communication(s) filed on 2 2a) This action is FINAL. 2b) 3 Since this application is in condition for allocation accordance with the practice und 	This action is non-final. owance except for formal m	·	merits is
Disposition of Claims			
 4) Claim(s) 1-21 is/are pending in the applica 4a) Of the above claim(s) is/are with 5) Claim(s) 21 is/are allowed. 6) Claim(s) 1-4 and 8-12 is/are rejected. 7) Claim(s) 5-7 and 13-20 is/are objected to. 8) Claim(s) are subject to restriction and continuous formula is a subject to restriction and continuous fo	drawn from consideration.		
Application Papers			
9) ☐ The specification is objected to by the Exar 10) ☑ The drawing(s) filed on 12 July 2001 is/are: Applicant may not request that any objection to Replacement drawing sheet(s) including the co 11) ☐ The oath or declaration is objected to by the	a)⊠ accepted or b)□ ob the drawing(s) be held in abe rrection is required if the draw	yance. See 37 CFR 1.85(a). ing(s) is objected to. See 37 CFR	` '
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for form a) All b) Some * c) None of: 1. Certified copies of the priority docum 2. Certified copies of the priority docum 3. Copies of the certified copies of the application from the International But * See the attached detailed Office action for a	nents have been received. nents have been received in priority documents have be reau (PCT Rule 17.2(a)).	n Application No en received in this National S	tage
Attachment(s) 1) ☑ Notice of References Cited (PTO-892) 2) ☑ Notice of Draftsperson's Patent Drawing Review (PTO-948 3) ☑ Information Disclosure Statement(s) (PTO-1449 or PTO/SE) Paper N 3/08) 5) Notice	w Summary (PTO-413) lo(s)/Mail Date of Informal Patent Application (PTO-1	52)
Paper No(s)/Mail Date	6) Other:	* * * * * * * * * * * * * * * * * * * *	

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1 – 3, 8, 9, 10, 11, are rejected under 35 U.S.C. 102(b) as being anticipated by Kameyama et al. (US Patent 5296388).
- 3. Kameyama et al. (fig. 2) teach producing a doping (112) at a surface silicon substrate (106P) by arsenic ion implantation, wherein the doping destroys a natural oxide on the semiconductor substrate and transforms the doped region (112) into an amorphous structure (col. 8 lines 5-13), after the doping, depositing a polysilicon layer (114) at the surface (fig. 3), and then annealing to produce an epitaxial layer and a buried doping (col. 8 lines 14 – 35). Kameyama et al. further teach the doping can be achieved by ion implantation with ions selected from Si. Ge. and Ar (col. 17 lines 26 -37). The semiconductor substrate comprising of silicon (col. 8 lines 64 –68).

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

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invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

- 5. Claims 4 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kameyama et al. (US Patent 5296388).
- 6. The Kameyama et al. reference teaches the feature previously outlined, but lacks the amorphous layer to have a thickness of 500 1000 nm, and depositing the polysilicon layer by LPCVD.
- 7. However, it would have been obvious to one of ordinary skill in the art at the time the invention was made to deposit the amorphous layer to a thickness of 500 1000 nm, and depositing the polysilicon layer by LPCVD, since it has been held that provision for adjustability where needed, involves only routine skill in the art. In re Stevens, 101 USPQ 284 (CCPA 1954).
- 8. Claims 5-7, and 13-20 are objected to as being dependent upon a rejected claim, but would be allowable if rewritten in independent form.
- 9. Claim 21 is allowable, because prior does not teach inter alia a polycrystalline or amorphous layer on a doped surface subjected to ion bombardment or RTA ,and further subjected to heat treatment to produce a MOS transistor.

Remarks

10. Applicant's arguments filed June 29, 2004 have been fully considered but they are not persuasive. Kameyama et al. is not doping through the oxide, rather oxide (108) is used as a mask for doping through the aperture (see fig. 2, & col. 7 lines 64 – 67). The Declaration filed on June 29, 2004 under 37 CFR 1.131 is sufficient to overcome the Yu reference.

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Contact Information

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (571) 272-1887. The examiner can normally be reached on M - F 8:30am - 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (751) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Igwe U. Anya Examiner Art Unit 2825

IA

March 19, 2004

MATTHEW SMITH
SUPERVISORY PATENT EVAMINER
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